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Amalt B

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :  
Hironobu KON et al : GROUP ART UNIT:  
SERIAL NO. 09/684,904 :  
FILED: October 10, 2000 : EXAMINER:  
FOR: VOLTAGE-DRIVEN POWER :  
SEMICONDUCTOR DEVICE :

SUPPLEMENTAL PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Prior to examination on the merits, and further to the Preliminary Amendment filed on October 10, 2000, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel Claims 19-22, without prejudice or disclaimer.

Please add new Claims 23-30, as follows:

RECEIVED  
DEC 12 2000  
TC 2800 MAIL ROOM

B1  
--23. (New) An injection enhanced gate transistor (IEGT) made of a semiconductor chip, comprising:  
a collector formed on one side of said semiconductor chip;  
a gate formed on an opposing side which opposes said one side of the semiconductor chip;  
a main emitter formed on said opposing side of the semiconductor chip; and